

RD151TS501US

PLL clock generator series

REJ03D0897-0102 Rev.1.02 Apr 25, 2007

Description

RD151TS501US is phase-locked loop clock generator with high-performance. And RD151TS501US is low-jitters and will enable high density mounting by shrink small-size package (SSOP-8).

Features

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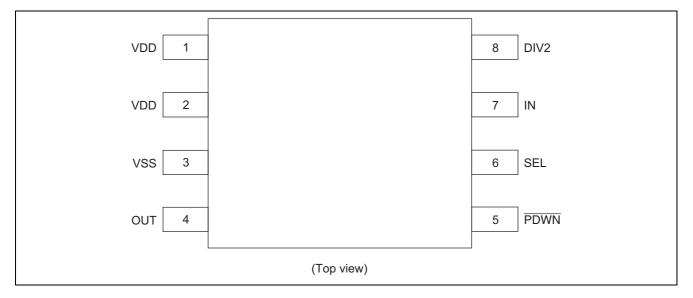
- Input frequency: 27.0 to 36.0 MHz
 - Output frequency:
 54.0 to 72.0 MHz (1 : 2), 67.5 to 72.0 MHz (1 : 2.5)
 - 27.0 to 36.0 MHz (1 : 1), 33.75 to 36.0 MHz (1 : 1.25) (Selectable)

Key Specifications

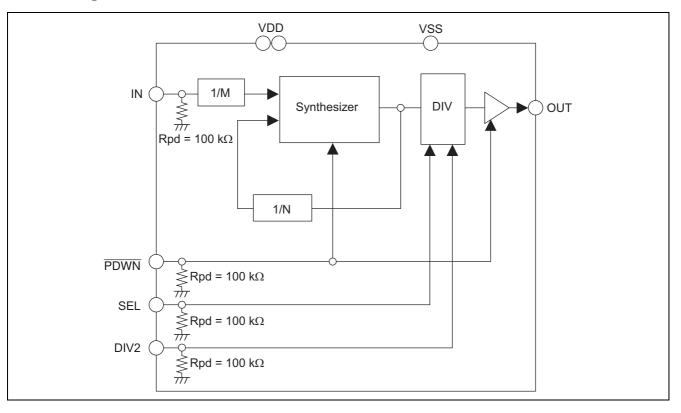
- Supply voltages: $V_{DD} = 2.7$ to 3.6 V
- Operating temperature = -10 to 75 °C
- Cycle to cycle jitter = ± 75 ps typ.
- Clock output duty cycle = $50\pm5\%$
- Stabilization time: 2ms max
- Power-down mode is supported
- Ordering Information

Part Name	Package Type	Package Code (Previous Package Code)	Package Abbreviation	Taping Abbreviation (Quantity)
RD151TS501USE	SSOP-8 pin	PVSP0008KA–A (TTP-8DBV)	US	E (3,000 pcs / Reel)

Pin Arrangement



Block Diagram



Pin Descriptions

Pin name	No.	Туре	Description	
VDD	1,2	Power	Power supply	
VSS	3	Ground	GND	
OUT	4	Output	Clock signal output	
PDWN	5	Input	Power-down control *1	
SEL	6	Input	Frequency select *1	
IN	7	Input	Clock signal input *1	
DIV2	8	Input	Frequency select *1	

Note: 1. LVCMOS level input. Pull-down by internal resistor (100 k Ω).

Power-down Function Table

PDWN	IC Operating	OUTPUT	Remark
L	Power-down	Low level	Default *1
Н	Active	Clock signal output	

Note: 1. All Circuits are set stand-by condition.

Clock Frequency Table

SEL	DIV2	Output Frequency (IN:OUT Ratio)	Remark
L	L	54.0 to 72.0 MHz (1:2)	Default
Н	L	67.5 to 72.0 MHz (1:2.5)	*1
L	Н	27.0 to 36.0 MHz (1:1)	
Н	Н	33.75 to 36.0 MHz(1:1.25)	*1

Note: 1. In case of selection of "SEL = H", input frequency is limited 27 to 28.8 MHz.

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{DD}	-0.5 to 4.6	V	
Input voltage	VI	-0.5 to 4.6	V	
Output voltage	Vo	–0.5 to V _{DD} +0.5	V	
Input clamp current *1	I _{IK}	-50	mA	V ₁ < 0
Output clamp current *1	I _{ОК}	-50	mA	V ₀ < 0
Continuous output current	lo	±50	mA	$V_0 = 0$ to V_{DD}
Maximum power dissipation	Pw	0.2	W	T _a = 25°C (in still air)
Storage temperature	T _{stg}	-65 to +150	°C	

Notes: Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied.

1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

Recommended Operating Conditions

ltem	Symbol	Min	Тур	Max	Unit	Conditions
Supply voltage	V _{DD}	2.7	3.3	3.6	V	
DC input signal voltage		-0.3		V _{DD} +0.3	V	
Operating temperature	Ta	-10		75	°C	

DC Electrical Characteristics

 $T_a = -10$ to 75 °C, $V_{DD} = 2.7$ to 3.6 V

ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Input voltage	VIL	—		0.8	V	IN, PDWN, SEL, DIV2 pins
input voltage	VIH	2.0	_	—	V	IN, PDWN, SEL, DIV2 pins
Input current	h	—	-	±100	μA	V _I = 0 V or 3.6 V, IN, PDWN, SEL, DIV2 pins
Input capacitance	Cı	—	3	_	pF	IN, PDWN, SEL, DIV2 pins
Output voltage	V _{OL}	—	_	0.5	V	V_{OL} = 1 mA, V_{DD} = 3.3 V, OUT pin
	V _{OH}	V _{DD} -0.2	_	V _{DD}	v	$V_{OH} = -1 \text{ mA}, V_{DD} = 3.3 \text{ V}, \text{ OUT pin}$
	IOL	—	15	—	mA	$V_{OL} = 1.65 \text{ V}, V_{DD} = 3.3 \text{ V}, \text{OUT pin}$
Output current	I _{OH}	—	-15	—	mA	$V_{OH} = 1.65 \text{ V}, V_{DD} = 3.3 \text{ V}, \text{OUT pin}$
Output impedance		—	30	—	Ω	OUT pin
Pull-down resister	R _{pd}	80 k	100 k	120 k	Ω	

Note: The condition of the minimum and maximum value must use the value specified under "Recommended Operating Conditions".

Parameters are target of design. Not 100% tested in production.

AC Electrical Characteristics

					Т	$r_a = -10$ to 75 °C, $V_{DD} = 2.7$ to 3.3 V	, C _L = 15 pF
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions	Notes
Operating current	I _{DD}	_	10	17	mA	V_{DD} = 3.3 V, \overline{PDWN} = 1, C_L = 0 pF, fout = 72MHz	
Stand-by current	I _{DDPD}	_	15	35	μΑ	$V_{DD} = 3.3 \text{ V}, \overline{\text{PDWN}} = 0, \text{ IN} = 0 \text{ V}$	
Cycle to cycle jitter	tccJ	_	75	_	ps	$C_L = 0 pF$	Figure 1
Frequency accuracy		-50	—	50	ppm		*1
Rise time / Fall time	t _r / t _f	0.7	1.5	6.0	ns	$V_{DD} = 3.3 \text{ V}, 0.2 \text{V}_{DD} \text{ to } 0.8 \text{V}_{DD}$	
Clock duty cycle	t _{DT}	45	50	55	%		
Stabilization time	t _{SB}	_	—	2	ms		*2

Notes: Parameters are target of design. Not 100% tested in production.

- 1. The accuracy of the output frequency to a set value.
- 2. Stabilization time is the time required for the integrated circuit to obtain phase lock of its input signal after power up.

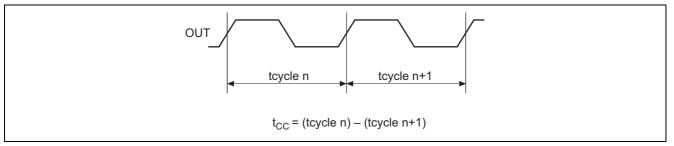


Figure 1 Cycle to cycle jitter

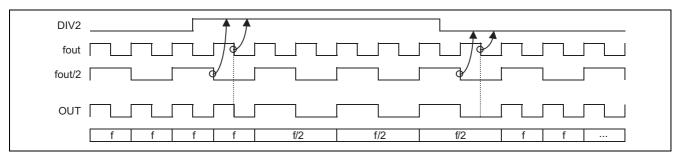


Figure 2 Timing chart

Recommended Circuit Configuration

The power supply circuit of the optimal performance on the application of a system should refer to Figure 3.

 V_{DD} decoupling is important to reduce Jitter performance.

The C1 decoupling capacitor should be placed as close to the VDD pin as possible, otherwise the increased trace inductance will negate its decoupling capability.

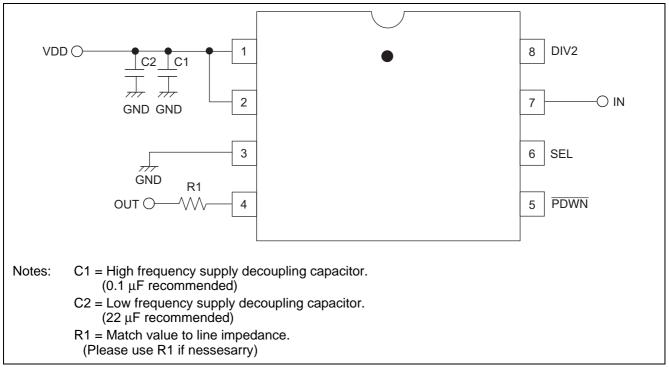


Figure 3 Recommended circuit configuration

Remark for use

Please do not use the pull-up resistance for the OUT terminal to prevent wrong operation of IC.

Package Dimensions

JEITA Package Code	RENESAS Code Previous Code MASS[Typ.]		
P-VSSOP8-2.3x2-0.50	PVSP0008KA-A TTP-8DB/TTP-8DBV 0.010g		
		be bbe bcontrolcon	Reference Symbol Dimension in Millimeters Min Nom Max D 1.8 2.0 2.2 E 2.2 2.3 2.4 A2 0.6 0.7 0.8 A1 0 0.1 A bp 0.15 0.22 0.3 b1 0.1 C 0.08 0.13 0.23 C1 HE 2.8 3.1 3.4 (E) (0.5) X Y Z Z L

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